COMPLIANT

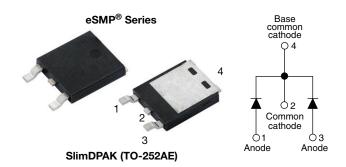
HALOGEN

FREE



## Vishay Semiconductors

# Hyperfast Rectifier, 2 x 4 A FRED Pt®



### **LINKS TO ADDITIONAL RESOURCES**



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	2 x 4 A			
V <sub>R</sub>	200 V			
V <sub>F</sub> at I <sub>F</sub>	0.71 V			
t <sub>rr</sub> (typ.)	16 ns			
T <sub>J</sub> max.	175 °C			
Package	SlimDPAK (TO-252AE)			
Circuit configuration	Common cathode			

#### **FEATURES**

- · Hyperfast recovery time
- 175 °C max. operating junction temperature
- Low forward voltage drop reduced Q<sub>rr</sub> and soft recovery
- · Low leakage current
- Very low profile typical height of 1.3 mm
- Polyimide passivation for high reliability standard
- · Ideal for automated placement
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS inverters or as freewheeling diodes. Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

### **MECHANICAL DATA**

Case: SlimDPAK (TO-252AE)

Molding compound meets UL 94 V-0 flammability rating

Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002

ABSOLUTE MAXIMUM RATINGS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage		V <sub>RRM</sub>		200	V
Average rectified forward current —	per leg	I <sub>F(AV)</sub>	T <sub>C</sub> = 167 °C	4	
Average rectilled forward current	per device			8	Α
Non-repetitive peak surge current per leg		I <sub>FSM</sub>	T <sub>J</sub> = 25 °C, 10 ms sine pulse wave	100	
Operating junction and storage temperatures		T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	$V_{BR}, V_{R}$	I <sub>R</sub> = 100 μA	200	-	-	
Forward voltage per leg	V <sub>F</sub>	I <sub>F</sub> = 4 A	=.	0.88	1.0	V
		I <sub>F</sub> = 8 A	-	0.97	1.14	
		I <sub>F</sub> = 4 A, T <sub>J</sub> = 150 °C	-	0.71	0.80	
		I <sub>F</sub> = 8 A, T <sub>J</sub> = 150 °C	=.	0.8	1.0	
Reverse leakage current per leg	I <sub>R</sub>	V <sub>R</sub> = V <sub>R</sub> rated	-	-	4	
		$T_J = 150 ^{\circ}\text{C},  V_R = V_R  \text{rated}$	-	-	80	μΑ
Junction capacitance per leg	C <sub>T</sub>	V <sub>R</sub> = 200 V	=.	17	=.	pF

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 A, dI_F/dt = 10$	00 A/μs, V <sub>R</sub> = 30 V	-	16	-	
Poverse receivery time		$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{RR} = 0.25 \text{ A}$		-	-	25	
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	20	-	ns
		T <sub>J</sub> = 125 °C		-	30	-	
Dook was a very a very ant	1	T <sub>J</sub> = 25 °C	$I_F = 4 A$	-	2.5	=.	Α
Peak recovery current I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 160 V	-	4	-	_ ^	
Doverso recovery charge	everse recovery charge Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	25	-	nC
neverse recovery charge		T <sub>J</sub> = 125 °C		=	60	-	110

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C
Thermal resistance, junction to ambient per diode	R <sub>thJA</sub> (1)(2)		-	73	90	°C/W
Thermal resistance, junction to mount per diode	R <sub>thJM</sub> <sup>(3)</sup>		-	2.1	2.5	°C/W
Marking device		Case style SlimDPAK (TO-252AE)		8CV	H02	•

#### **Notes**

- $^{(1)}$  The heat generated must be less than thermal conductivity from junction to ambient;  $dP_D/dT_J < 1$   $R_{thJA}$
- $^{(2)}$  Free air, mounted or recommended copper pad area; thermal resistance  $R_{thJA}$  junction to ambient
- (3) Mounted on infinite heatsink

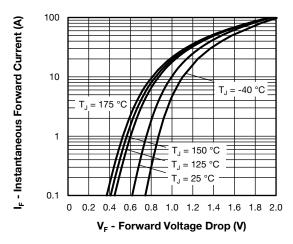


Fig. 1 - Typical Forward Voltage Drop Characteristics

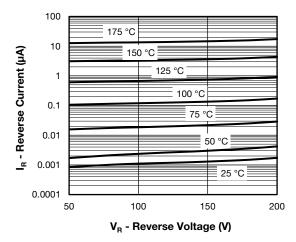


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

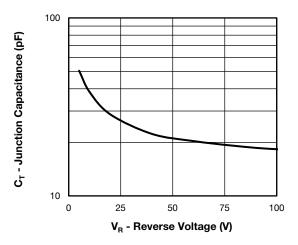


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

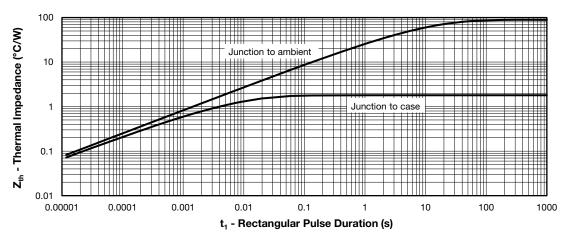


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

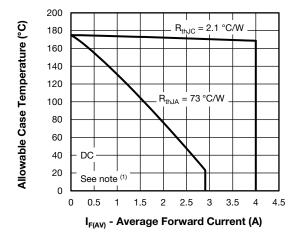


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

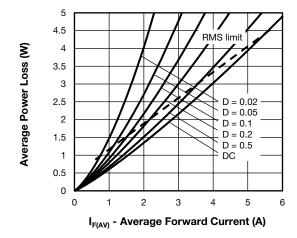


Fig. 6 - Forward Power Loss Characteristics

### Note

Formula used: T<sub>C</sub> = T<sub>J</sub> - (Pd + Pd<sub>REV</sub>) x R<sub>th,JC</sub>; Pd = forward power loss = I<sub>F(AV)</sub> x V<sub>FM</sub> at (I<sub>F(AV)</sub>/D) (see fig. 6); Pd<sub>REV</sub> = inverse power loss = V<sub>R1</sub> x I<sub>R</sub> (1 - D); I<sub>R</sub> at V<sub>R1</sub> = rated V<sub>R</sub>

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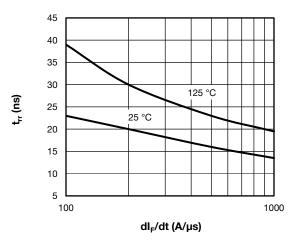


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

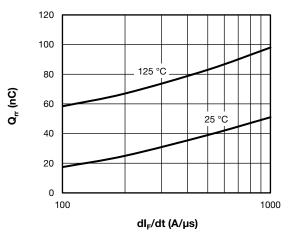
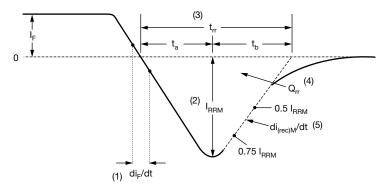


Fig. 8 - Typical Stored Charge vs. dl<sub>E</sub>/dt



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm l_{r}$  to point where a line passing through 0.75  $\rm l_{RRM}$  and 0.50  $\rm l_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

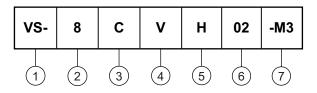
(5) di<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 9 - Reverse Recovery Waveform and Definitions



### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - Current rating (8 = 8 A)

3 - Circuit configuration:

C = common cathode

4 - V = SlimDPAK

5 - Process type,

H = hyperfast recovery

6 - Voltage code (02 = 200 V)

7 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

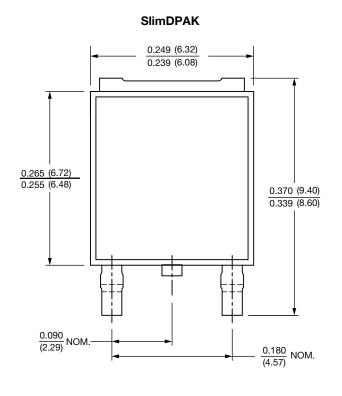
ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-8CVH02-M3/I	4500	4500	13"diameter plastic tape and reel		

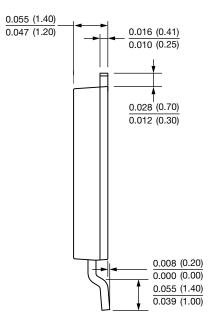
LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?96081</u>				
Part marking information	www.vishay.com/doc?96085			
Packaging information	www.vishay.com/doc?88869			



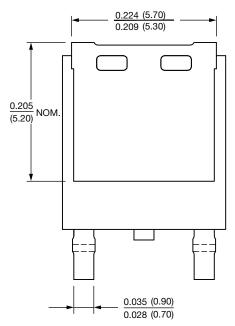
## **SlimDPAK**

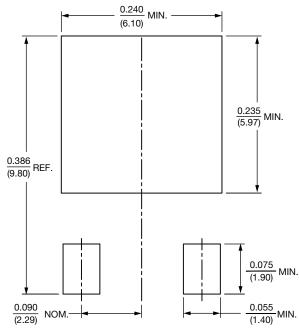
### **DIMENSIONS** in inches (millimeters)





### **Mounting Pad Layout**







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